

IEEE SW Test Workshop

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Trends, Challenges, and Solutions in Advanced SoC Wafer Probe





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Outline/Summary

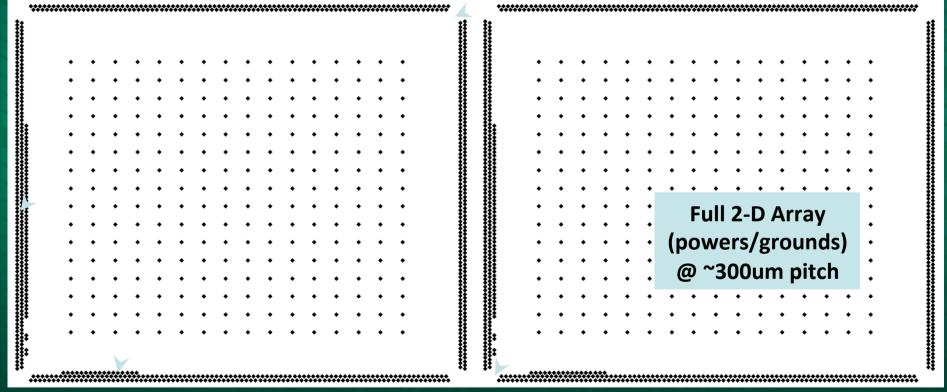
- Rapid recent adoption of advanced packaging
 - Copper pillar and C4 flipchip
- Driven by mobile cost and performance roadmaps
 - Customers relying on "more-than-Moore" advances
- Presents significant challenges for wafer test and probe
 - Layouts are fully-populated 2-D arrays at sub-100um pitches
 - Contacts are delicate structures made of new and diverse materials
 - Electrical performance (AC&DC) requirements continue to advance
 - Industry requires a "Moore-like" cost trajectory
- Solutions rely on a mixture of technologies from diverse areas
 - MEMS processing, materials science, signal integrity, etc.



Contemporary Packaging Layouts Demand a Vertical Probe Architecture

3 Rows @ ~80um min pitch (some 4-row designs in '13)

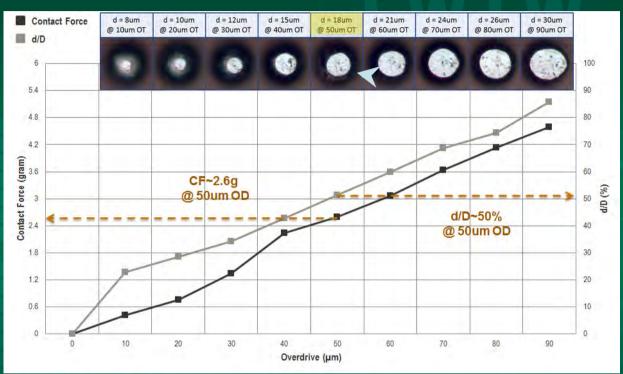
Minimal (~250um) corner keepouts

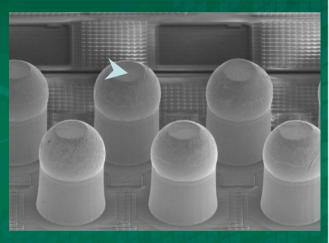




Example – x2 Card for 80um Copper Pillar Device

These 2-D Layouts Populated With Structures That Require Low Probe Forces





- Typical SnAg damage (d) requirement <50% of pillar diameter (D)
 - Additional requirements on probe mark topology (notching, smearing, etc.)
 - Imposed by assembly constraints (reliability)



• Met with probe forces of 2-3g for 30um < D < 40um

At Low Force, Probe Material and Geometry **Optimization Required for Stable Electrical Contact**

MEMS Probe #1

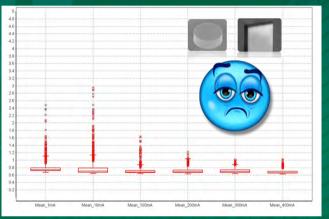


MEMS Probe #2



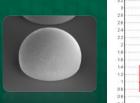
Bare Copper Pillar



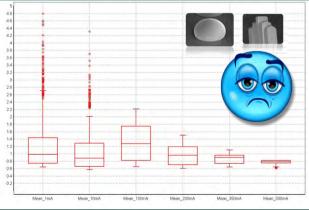


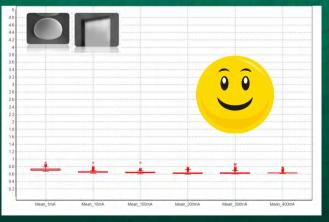
SnAg Bump





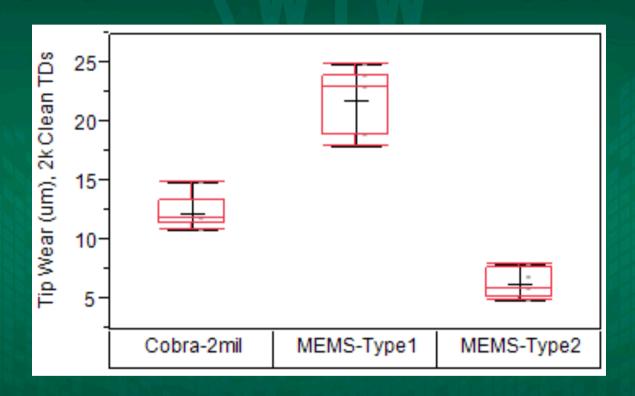






Source: Wittig et al, SWTW 2011

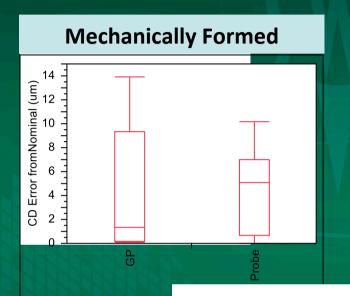
Overall Cost Also Strongly Influenced by Probe Material and Geometry

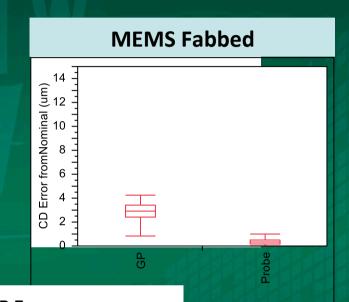


- 4x difference in wear/lifetime for different probes
 - Same (standard HVM) cleaning recipe used



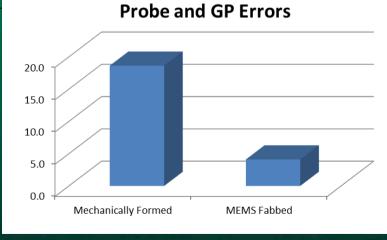
Dimensional Control Improved With MEMS-Based Fabrication Processes



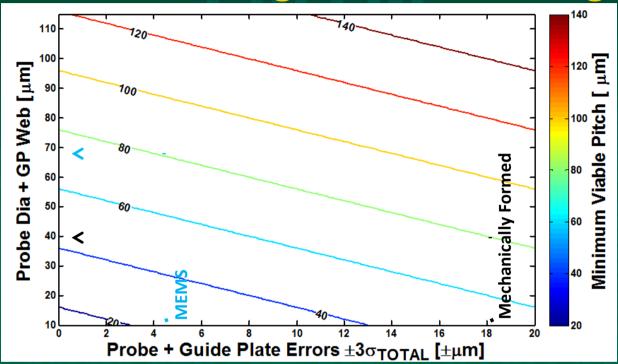


- Raw "as-fabbed" distributions
- Indicative of natural process capability





For Sub-100um Pitches, MEMS-based Dimensional Control Offers Significant Advantages



- Reduction in as-produced dimensional errors can be used in different ways:
 - Larger probe for a given design pitch for 80um example above, Δ =25um
 - Better electrical performance (current, impedance) and longer lifetime
 - Smaller minimum-viable pitch for a given probe
 - Improved design coverage and extendibility
 - Higher probe/GP component yield for cost reduction



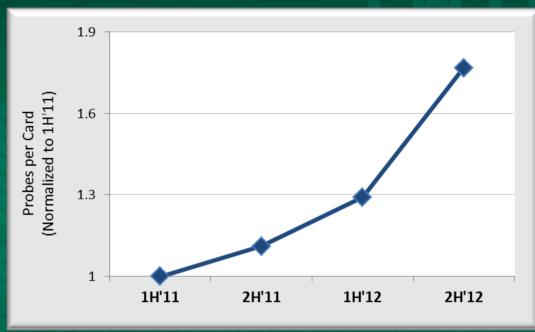
Composite MEMS Probes Enable Optimization of Mechanical and Electrical Characteristics



- Different materials, in different locations, doing different jobs
 - Analogous approach to composite design in other fields (eg, aerospace)
- Fabricated with semiconductor/MEMS lithography & direct-write technologies
 - Dimensional control ~5x
 improved over mechanical
 forming
 - Short cycle time customization



And On Top of It All, There are More and More of These Probes in Each Card



Implications

- Card will sample "tails" of probe+guideplate distributions
 - Cpk > 1.33 processes req'd
 - Or, cost and leadtime suffer
- Quality and process control systems become critical

Source: Internal MP/FFI MEMS Shipment Data

- Two primary drivers/causes (roughly equal influences)
 - 1. Increased parallelism more DUTs for test cost reduction
 - 2. Increased probes per DUT more test content and complexity per DUT



Component Count Increase a Reflection of Complexity-Per-DUT Increase



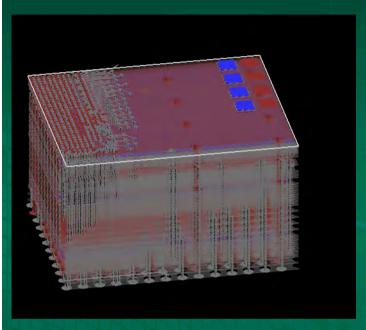
Source: Internal MP/FFI MEMS Shipment Data

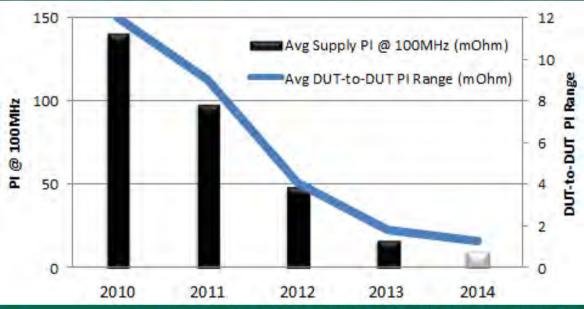
Implications

- Increase in PCB complexity design, validation, and fab
 - Simulation and validation tools/ processes key to error reduction (leadtime/OTD)
- Deploying PCB assembly+test technologies from other areas
 - Rapid advancement of standard
 SoC probecard PCB processes
- Primarily driven by increase in number and performance of critical power supplies
 - Particularly evident in low-power multi-core architectures



Impedance Performance of Power Supplies Critical to Yield of Low-Power Mobile Devices





- AC impedance of critical power supplies limiting wafer sort yield
 - Full 3-D simulation of probe-to-tester interconnect standard validation
- Continued advances in interconnect (MLC/MLO) required
 - Wired space transformers (and low-end MLCs) not viable in these apps



Summary – Trends, Challenges, and Solutions

- Trends and Challenges are directionally familiar
- But, these familiar directions are rapidly accelerating
 - 2-D Grid Array pitches below 100um
 - Bump/pad materials and structures demanding <2-3g of probe force
 - Continued improvement in contact stability performance
 - AC impedance reduction of 10x in 3 years
 - Exploding probe (2x in 2 years) and component (4x in 2 years) counts
 - Continuing cost and leadtime reductions
- Solutions encompass a spectrum of technologies and processes
 - Composite MEMS structures
 - Sophisticated electrical design, validation, and test tools+processes
 - Semiconductor-inspired process control and quality systems

